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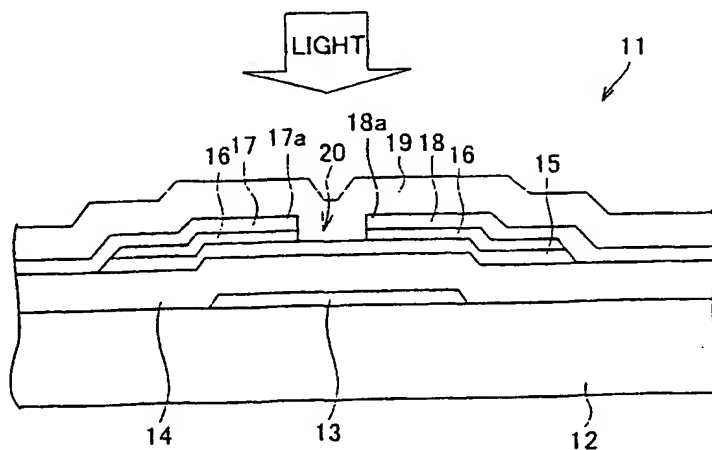
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(54) Title: THIN FILM PHOTOTRANSISTOR, ACTIVE MATRIX SUBSTRATE USING THE PHOTOTRANSISTOR, AND IMAGE SCANNING DEVICE USING THE SUBSTRATE



(57) Abstract: A gate insulation film (14) and a semiconductor layer (15) are laminated on a gate electrode (13); and a source electrode (17) and a drain electrode (18) are formed on the semiconductor layer (15) by having a predetermined interval between their end portions. Each of the source electrode (17) and the drain electrode (18) includes a superimposition area (17a and 18a), and at least one portion of the superimposition area (17a and 18a) has translucency. This arrangement realizes improvement of photosensitivity (I_p/I_d) without causing complication of wiring layout or manufacturing process.